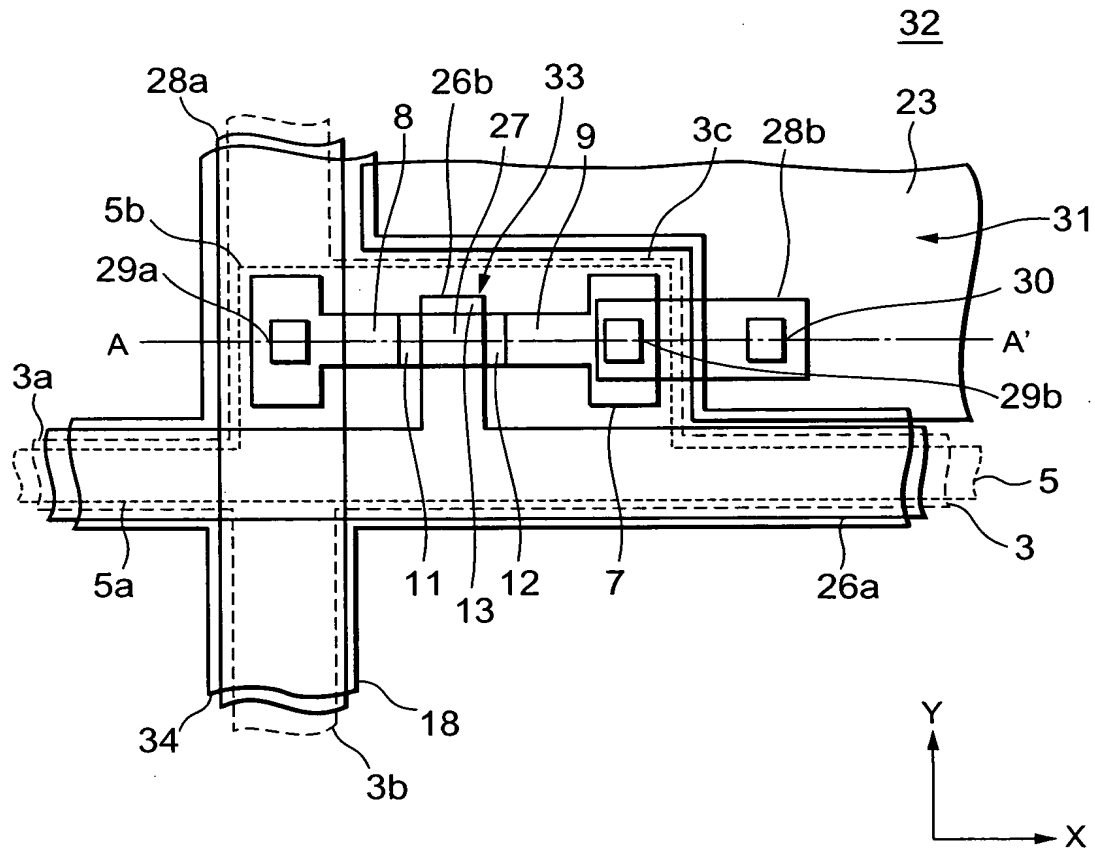
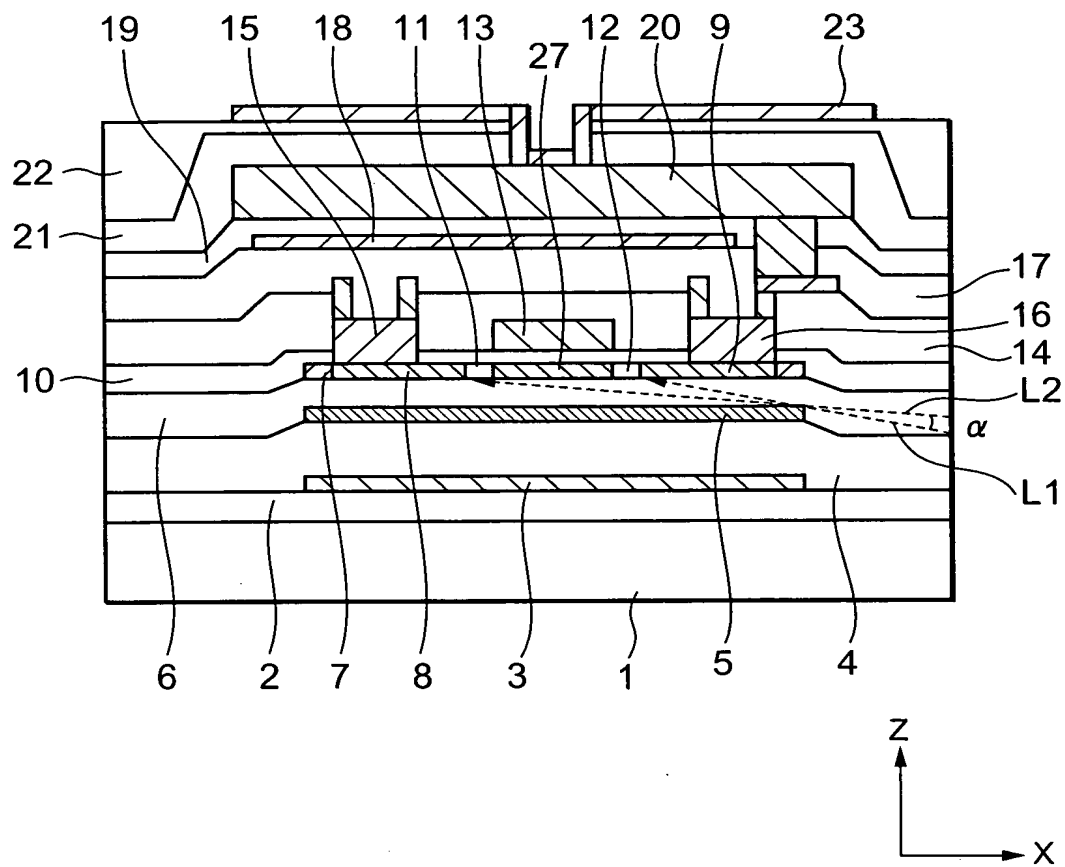


A cross-sectional view of a semiconductor device. The device consists of a substrate with a bottom layer L11 and a top layer L12. A patterned layer 451 is formed on the substrate. A dashed line indicates an angle β between the top surface of the patterned layer 451 and the top surface of the substrate. A coordinate system (X, Y) is shown at the bottom right.





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Fig. 4(a)

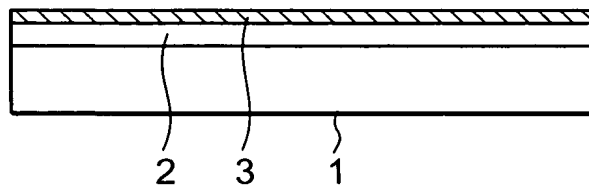


Fig. 4(b)

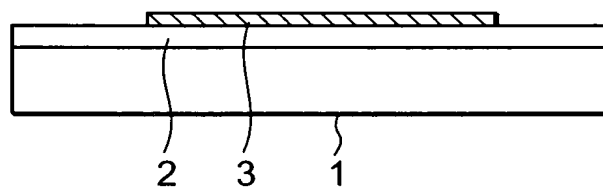


Fig. 4(c)

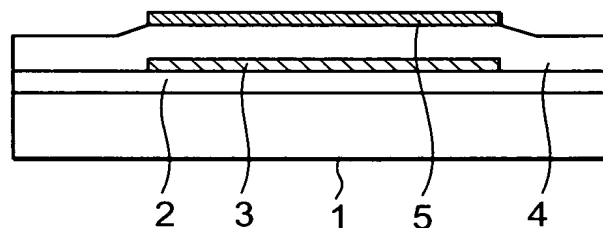
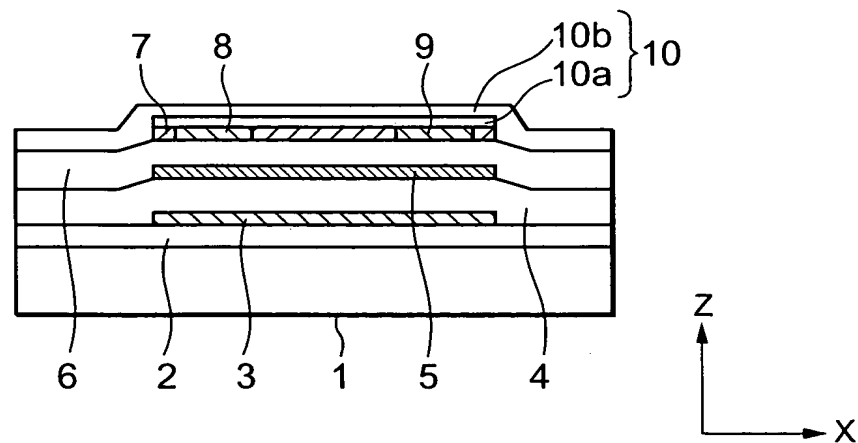
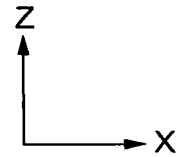
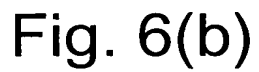
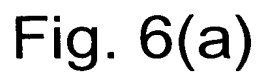


Fig. 4(d)



[illegible]



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Fig. 7(a)

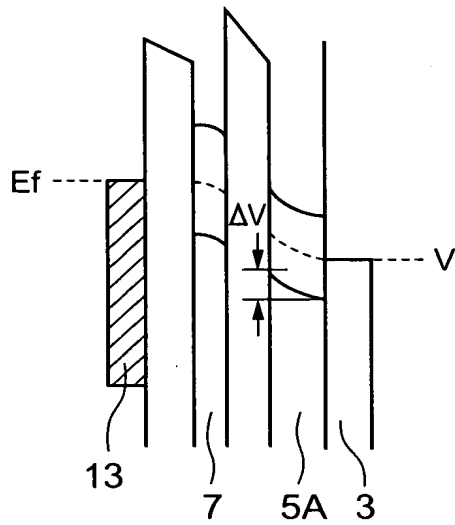


Fig. 7(b)

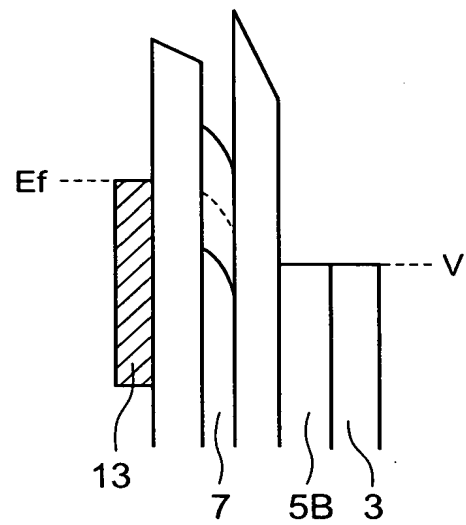
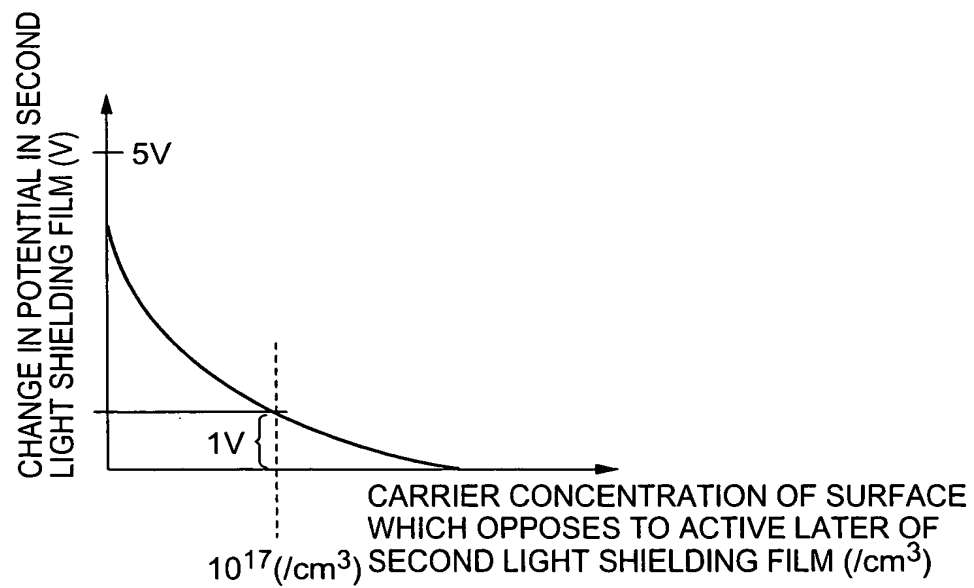
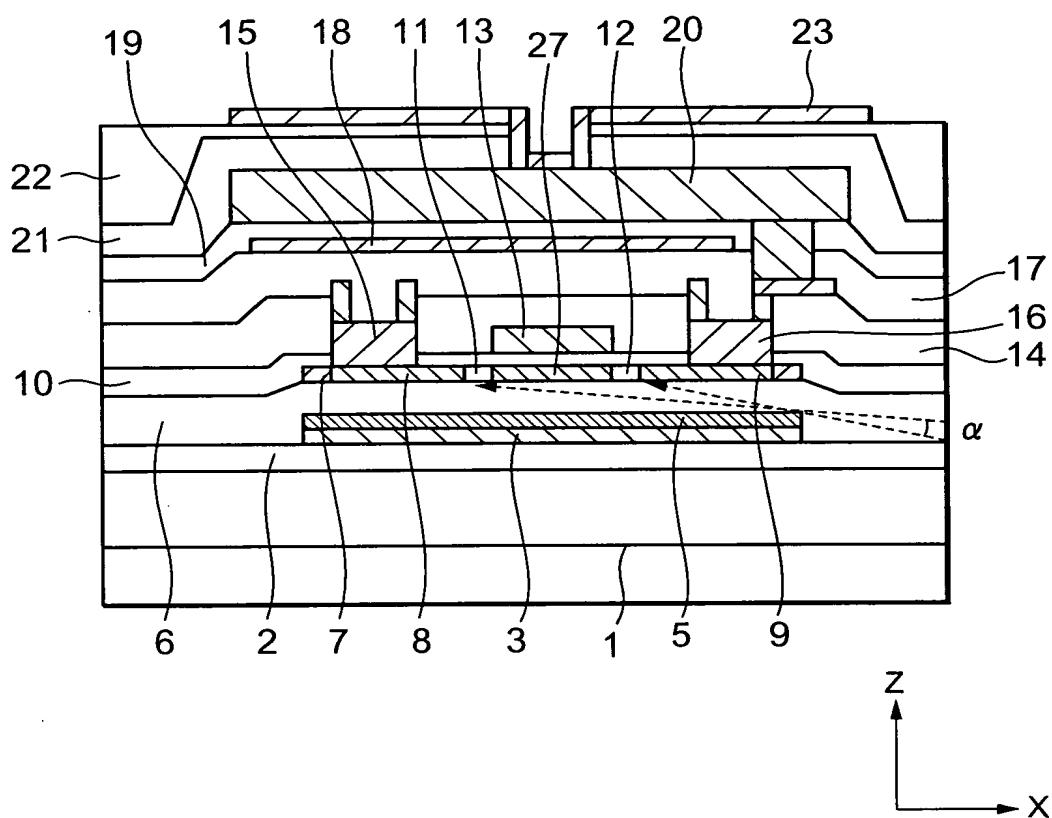


Fig. 8





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Fig. 10(a)

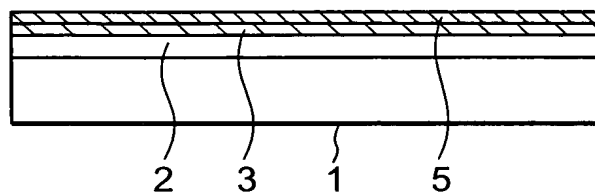
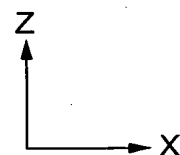
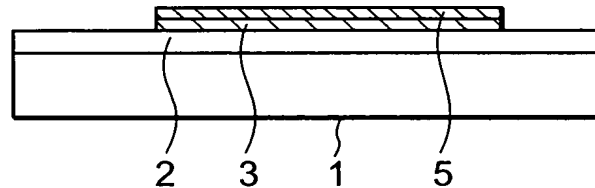
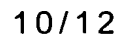


Fig. 10(b)





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Fig. 12

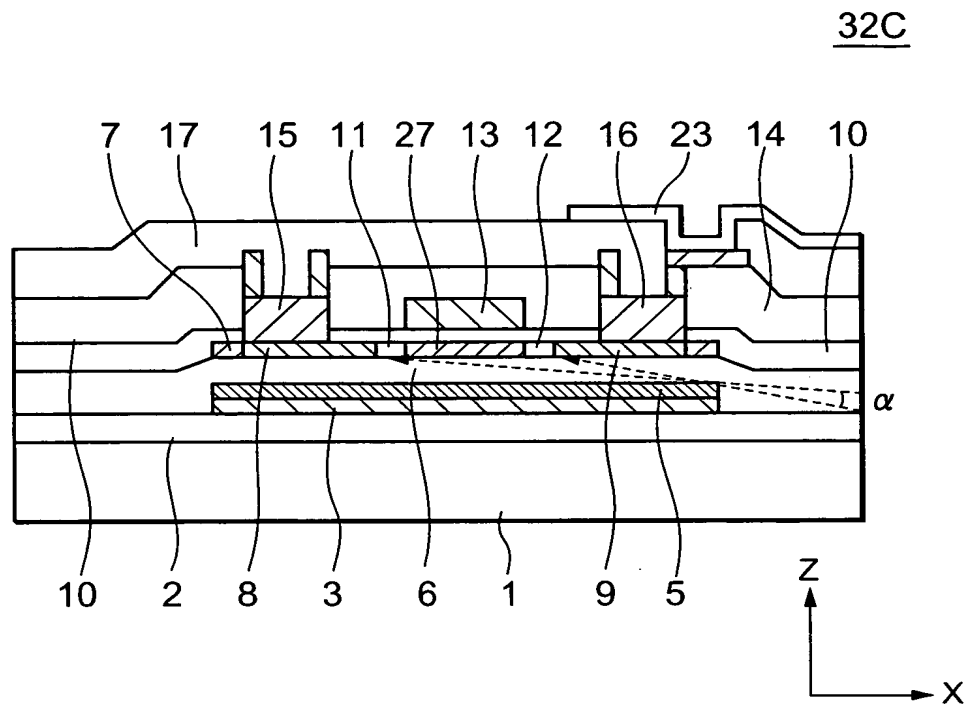
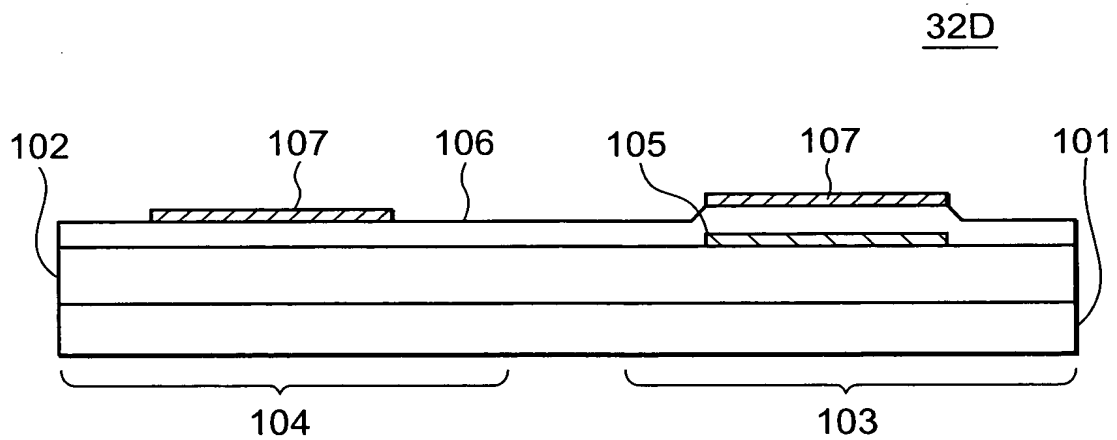


Fig. 13



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Fig. 14

